5SDD 31H6000

Old part no. DV 889-3300-60

High Voltage Diode

Properties

- Industry standard housing
- Suitable for parallel operation
- High operating temperature
- Low forward voltage drop

Key Parameters

V_{RRM}	=	6 000	V
I_{FAVm}	=	3 201	A
I_{FSM}	=	40 000	A
V_{TO}	=	0.944	V
r_T	=	0.166	mΩ

Applications

- Rectifier bridges

Types

	V_{RRM}
5SDD 31H6000	**6 000 V**
Conditions:	*T_j = -40 ÷ 150 °C, half sine waveform, f = 50 Hz*

Mechanical Data

F_m	**Mounting force**	**50 ± 5 kN**
m	**Weight**	**0.9 kg**
D_S	**Surface creepage distance**	**40 mm**
D_a	**Air strike distance**	**20 mm**

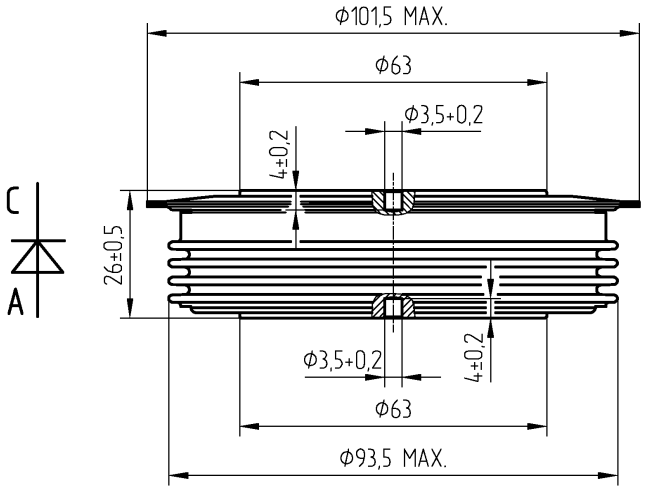

Fig. 1 Case

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Maximum Ratings			Maximum Limits	Unit
V_{RRM}	**Repetitive peak reverse voltage** *T_j = -40 ÷ 150 °C*		**6 000**	**V**
I_{FAVm}	**Average forward current** *T_c = 85 °C*		**3 201**	**A**
I_{FRMS}	**RMS forward current** *T_c = 85 °C*		**5 028**	**A**
I_{RRM}	**Repetitive reverse current** *$V_R = V_{RRM}$*		**120**	**mA**
I_{FSM}	**Non repetitive peak surge current** *V_R = 0 V, half sine pulse*	*t_p = 8.3 ms*	**42 700**	**A**
		t_p = 10 ms	**40 000**	**A**
I^2t	**Limiting load integral** *V_R = 0 V, half sine pulse*	*t_p = 8.3 ms*	**7 577 200**	**A^2s**
		t_p = 10 ms	**8 000 000**	**A^2s**
T_{jmin} **-** T_{jmax}	**Operating temperature range**		**-40 ÷ 150**	**°C**
T_{STG}	**Storage temperature range**		**-40 ÷ 150**	**°C**

Unless otherwise specified T_j = 150 °C

Characteristics		Value			Unit
		min	typ	max	
V_{T0}	**Threshold voltage**			**0.944**	**V**
r_T	**Forward slope resistance** *I_{F1} = 4 869 A, I_{F2} = 14 608 A*			**0.166**	**mΩ**
V_{FM}	**Maximum forward voltage** *I_{FM} = 4 000 A*			**1.600**	**V**
Q_{rr}	**Recovered charge** *V_R = 100 V, I_{FM} = 2000 A, di_F/dt = -30 A/µs*		**6 500**		**µC**

Unless otherwise specified T_j = 150 °C

Thermal Parameters			*Value*	*Unit*
R_{thjc}	**Thermal resistance junction to case**	*double side cooling*	**8.0**	**K/kW**
		anode side cooling	**14.5**	
		cathode side cooling	**18.0**	
R_{thch}	**Thermal resistance case to heatsink**	*double side cooling*	**2.5**	**K/kW**
		single side cooling	**5.0**	

Transient Thermal Impedance

Analytical function for transient thermal impedance

$$Z_{thjc} = \sum_{i=1}^{4} R_i (1 - \exp(-t / \tau_i))$$

Conditions:
F_m = 50 ± 5 kN, Double side cooled

Correction for periodic waveforms

180°	**sine:**	**1.0 K/kW**
120°	**sine:**	**1.5 K/kW**
60°	**sine:**	**2.5 K/kW**
180°	**rectangular:**	**0.9 K/kW**
120°	**rectangular:**	**1.5 K/kW**
60°	**rectangular:**	**2.5 K/kW**

i	1	2	3	4
τ_i (s)	0.4406	0.1045	0.0092	0.0022
R_i(K/kW)	4.533	2.255	0.868	0.345

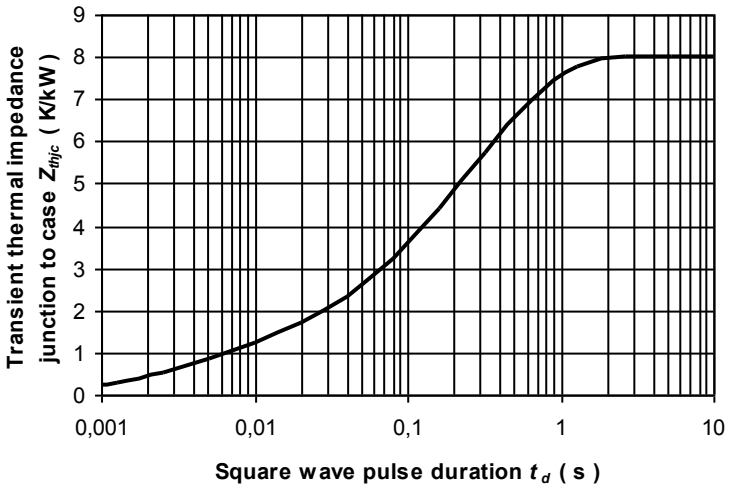

Fig. 2 Dependence transient thermal impedance junction to case on square pulse

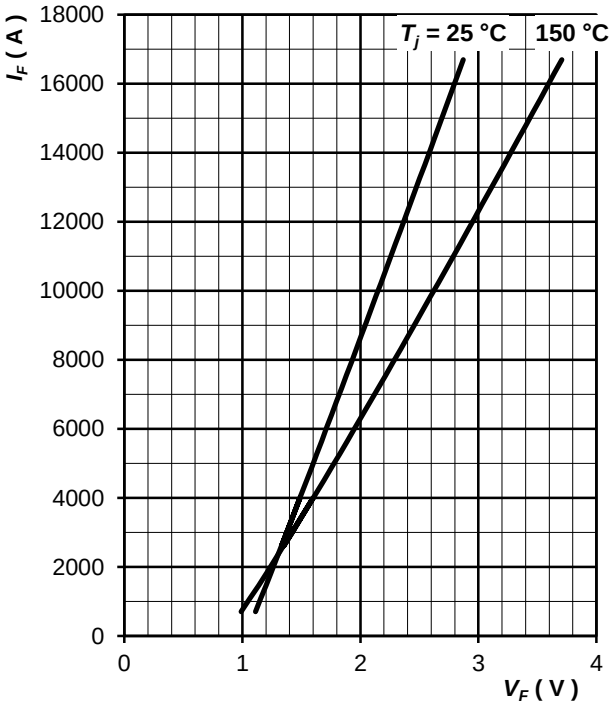

Fig. 3 Maximum forward voltage drop characteristics

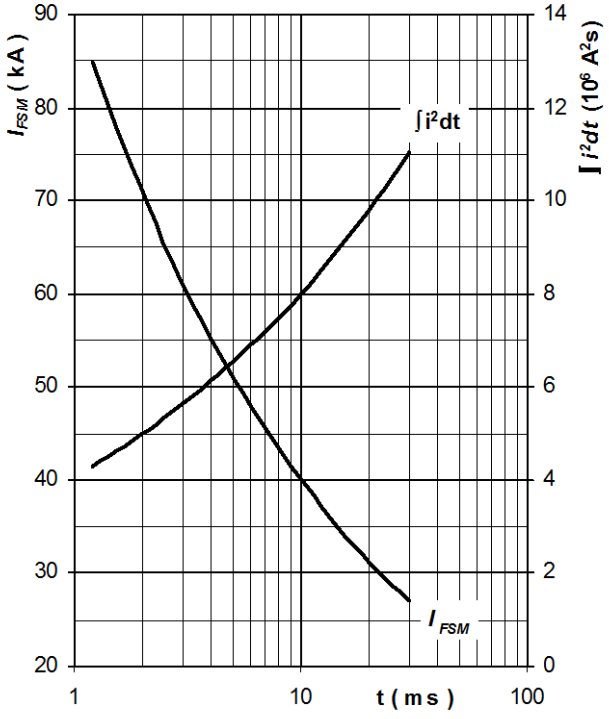

Fig. 4 Surge forward current vs. pulse length, half sine wave, single pulse, V_R = 0 V, $T_j = T_{jmax}$

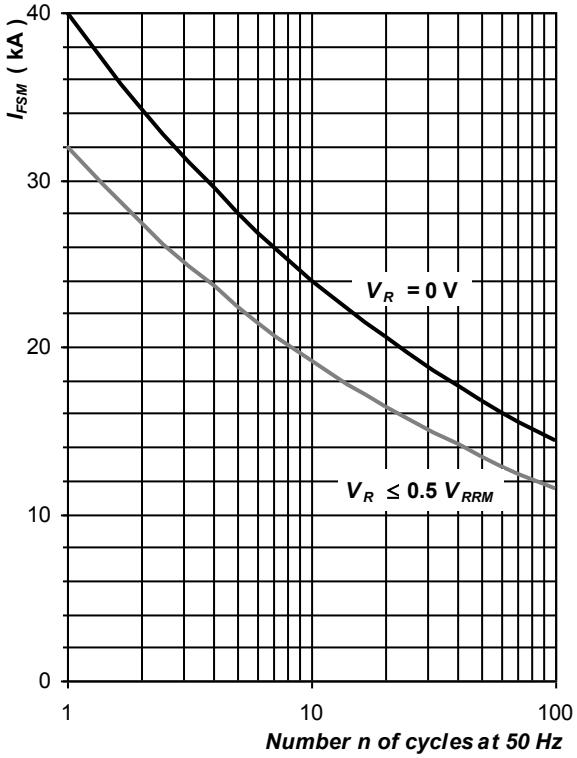

Fig. 5 Surge forward current vs. number of pulses, half sine wave, $T_j = T_{jmax}$

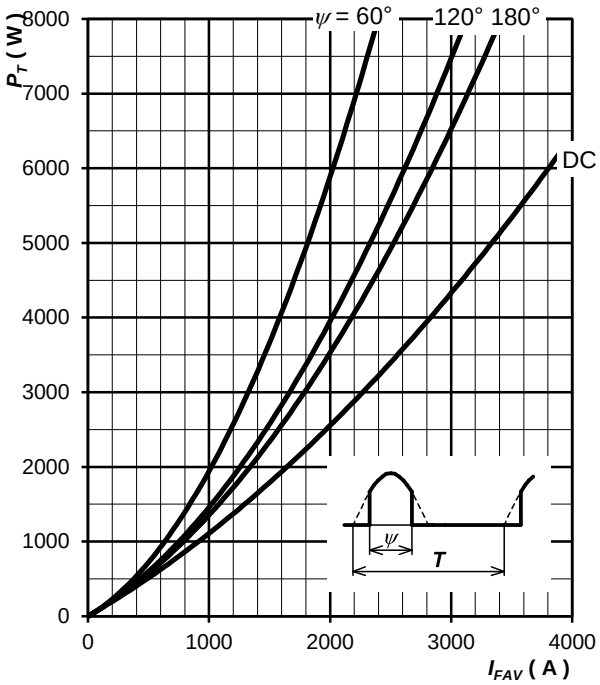

Fig. 6 Forward power loss vs. average forward current, sine waveform, f = 50 Hz, T = 1/f

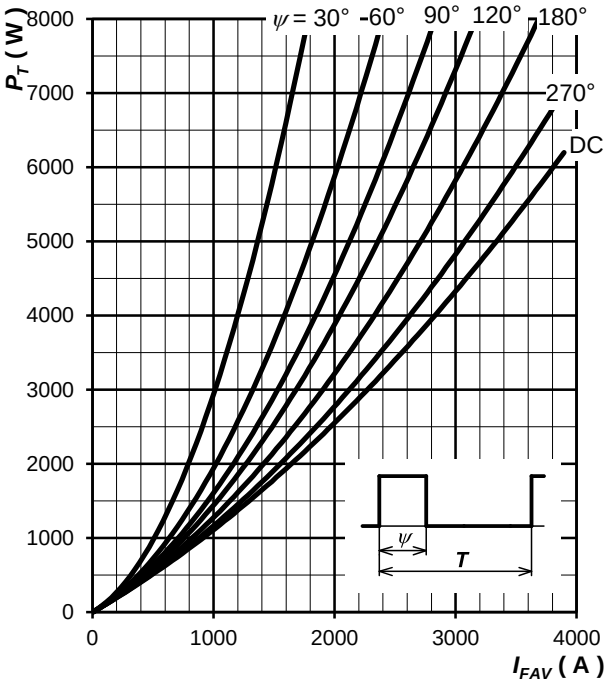

Fig. 7 Forward power loss vs. average forward current, square waveform, f = 50 Hz, T = 1/f

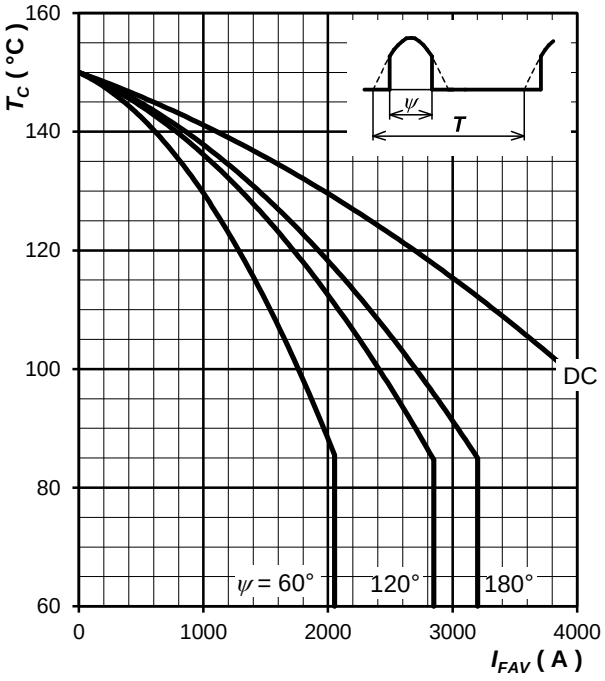

Fig. 8 Max. case temperature vs. aver. forward current, sine waveform, f = 50 Hz, T = 1/f

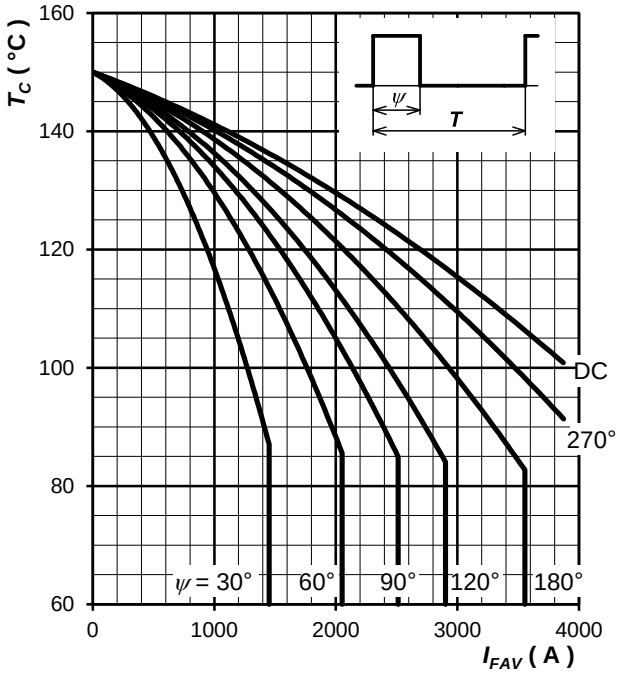

Fig. 9 Max.case temperature vs. aver. forward current, square waveform, f = 50 Hz, T = 1/f

Notes: